

TECHNICAL DATA DATA SHEET 721, REV -

HERMETIC POWER MOSFET P-CHANNEL

FEATURES:

DATING

- -100 Volt, 0.22 Ohm MOSFET
- Isolated and Hermetically Sealed
- Simple Drive Requirements

MAXIMUM RATINGS

ALL RATINGS ARE AT T_A = 25°C UNLESS OTHERWISE SPECIFIED.

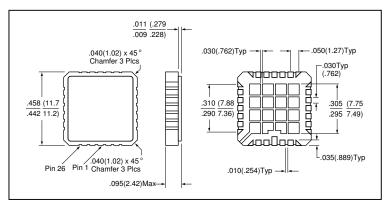
SYMBOL MIN TYP MAX UNITS

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT V _{GS} =10V, T _C = 25°C	I _D	-	-	-14	Amps
$V_{GS}=10V, T_{C}=100^{\circ}C$				-9.5	
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	1.36	°C/W
TOTAL DEVICE DISSIPATION @ T _C = 25°C	P_{D}	-	-	90	Watts
ELECTRICAL CHARACTERISTICS					
DRAIN TO SOURCE BREAKDOWN VOLTAGE	BV _{DSS}	-100	-	-	Volts
$V_{GS} = 0V$, $I_D = 1.0mA$					
DRAIN TO SOURCE ON STATE RESISTANCE	_	-	-		Ω
$V_{GS} = -10V, I_D = -9.5A$	$R_{DS(ON)}$			0.22	
$V_{GS} = -10V, I_D = -14A$	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	0.0		0.24	Malta
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = -250\mu A$	V _{GS(th)}	-2.0	-	-4.0	Volts
FORWARD TRANSCONDUCTANCE	g _{fs}	6.2	-	-	$S(1/\Omega)$
$V_{DS} \ge -15V$, $I_{DS} = -9.5A$ ZERO GATE VOLTAGE DRAIN CURRENT					^
$V_{DS} = 0.8$ xMax. Rating, $V_{GS} = 0$ V	I _{DSS}	-	-	-25	μΑ
$V_{DS} = 0.8xMax$. Rating	1088			-250	
$V_{GS} = 0V, T_{J} = 125^{\circ}C$					
GATE TO SOURCE LEAKAGE FORWARD @ RATED	I _{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE V _{GS}				-100	
TOTAL GATE CHARGE $V_{GS} = -10 \text{ V}$,	Q_g	31	-	60	nC
GATE TO SOURCE CHARGE $V_{DS} = .5X \text{ max. rating},$	Q_{gs}	3.7		13	
GATE TO DRAIN CHARGE $I_D = .5 \text{ x rated } I_D$	Q_{gd}	7.0		35.2	
TURN ON DELAY TIME $V_{DD} = -50V$	t _{d(ON)}	-	-	35	nsec
RISE TIME I _D = 14A	t _r			85 85	
TURN OFF DELAY TIME $R_{G} = 9.1\Omega$ FALL TIME	$t_{\sf d(ON)} \ t_{\sf f}$			65	
DIODE FORWARD VOLTAGE $T_J = 25^{\circ}C$, $I_S = 14A$,	V _{SD}	_	_	-4.2	Volts
$V_{GS} = 0V$	V SD	_	_	-4.2	VOILS
DIODE REVERSE RECOVERY TIME T _J = 25°C	t _{rr}	_	_	280	nsec
REVERSE RECOVERY CHARGE I _f = 14A	Q _{rr}			3.6	μC
di/dt = -100A/sec					F
INPUT CAPACITANCE V _{GS} = 0 Volts	C _{iss}	-	1400	-	pF
OUTPUT CAPACITANCE $V_{DS} = 25 \text{ Volts}$	Coss		600		•
REVERSE TRANSFER CAPACITANCE f = 1 MHz	C_{rss}		200		

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MECHANICAL DIMENSIONS: in Inches / m



LCC-28T

PINOUT TABLE

	PINS(S) 1 & 15-28	PINS 5-11	PINS 2, 3, 13, & 14
MOSFET - LCC-28T	SOURCE	DRAIN	GATE



TECHNICAL DATA

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